

FIG. 1A (PRIOR ART)

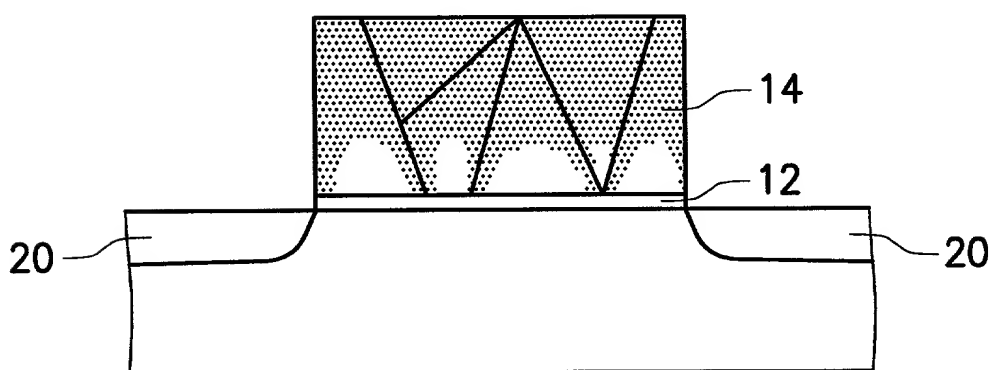


FIG. 1B (PRIOR ART)

A cross-sectional view of a semiconductor device. A substrate 20 is shown with a thin layer 12 on its top surface. A patterned layer 14 is formed on top of layer 12, featuring a series of triangular peaks. The layer 14 is filled with a stippled pattern, and the peaks are defined by solid lines.

FIG. 2 (PRIOR ART)

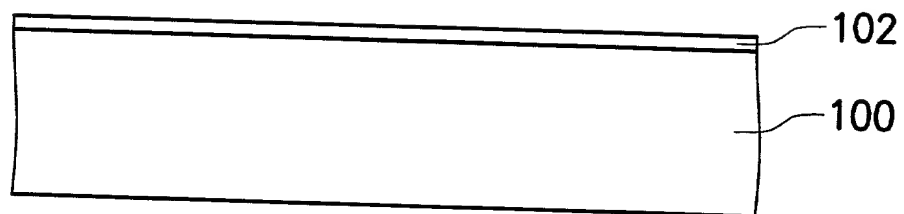


FIG. 3A

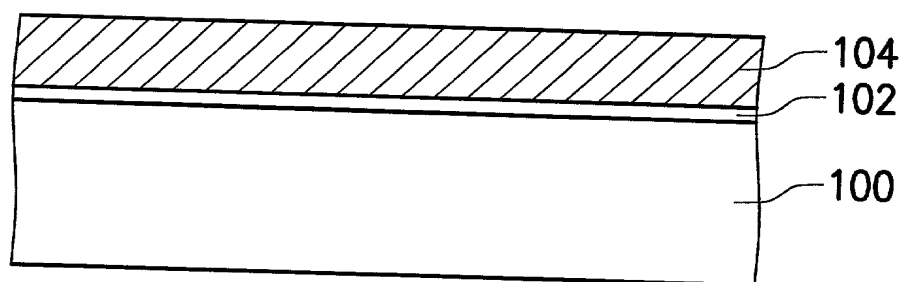


FIG. 3B

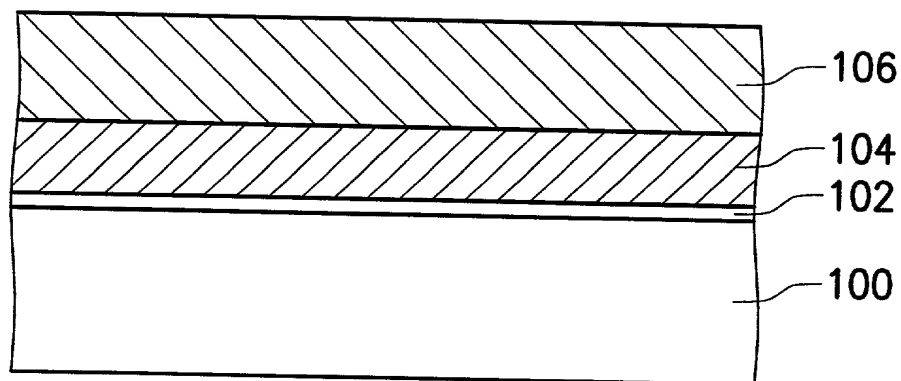


FIG. 3C

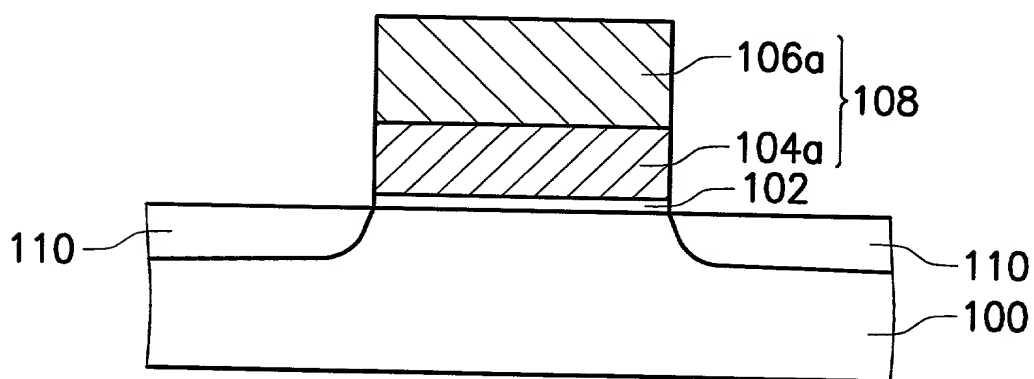


FIG. 3D